

Veena Misra

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/4563746/publications.pdf>

Version: 2024-02-01

168
papers

3,682
citations

126858

33
h-index

155592

55
g-index

169
all docs

169
docs citations

169
times ranked

4197
citing authors

#	ARTICLE	IF	CITATIONS
1	Bias Temperature Instability on SiC n- and p-MOSFETs for High Temperature CMOS Applications. , 2022, , .		1
2	Flexible thermoelectric generator with liquid metal interconnects and low thermal conductivity silicone filler. Npj Flexible Electronics, 2021, 5, .	5.1	44
3	Wearable skin vapor sensing system for continuous monitoring of various health and lifestyles. , 2021, , .		3
4	Evaluation of Environmental Enclosures for Effective Ambient Ozone Sensing in Wrist-worn Health and Exposure Trackers. , 2021, , .		0
5	A Pipeline for Adaptive Filtering and Transformation of Noisy Left-Arm ECG to Its Surrogate Chest Signal. Electronics (Switzerland), 2020, 9, 866.	1.8	7
6	Engineering a Unified Dielectric Solution for AlGaIn/GaN MOS-HFET Gate and Access Regions. IEEE Transactions on Electron Devices, 2020, 67, 881-887.	1.6	6
7	Flexible thermoelectric generators for body heat harvesting “ Enhanced device performance using high thermal conductivity elastomer encapsulation on liquid metal interconnects. Applied Energy, 2020, 262, 114370.	5.1	113
8	Preliminary Assessment of Human Biological Responses to Low-level Ozone. , 2020, , .		0
9	A novel monolithic array of multiple metal oxide sensors for E-Nose applications via selective on-chip annealing of nanolayered ALD stacks. , 2019, , .		1
10	Optimizing the energy balance to achieve autonomous self-powering for vigilant health and IoT applications. Journal of Physics: Conference Series, 2019, 1407, 012001.	0.3	5
11	Effects of LaSiO ₃ Thickness and Forming Gas Anneal Temperature on Threshold Voltage Instability of 4H-SiC MOSFETs With LaSiO ₃ . IEEE Transactions on Electron Devices, 2019, 66, 539-545.	1.6	1
12	Improvement of Threshold Voltage Reliability of 4H-SiC MOSFETs With Lanthanum Silicate by High Temperature Forming Gas Anneal. IEEE Electron Device Letters, 2018, 39, 244-247.	2.2	7
13	Investigation of O ₃ Adsorption on Ultra-Thin ALD SnO ₂ by QCM. IEEE Sensors Journal, 2018, 18, 3590-3594.	2.4	5
14	On Using the Volatile Mem-Capacitive Effect of TiO ₂ Resistive Random Access Memory to Mimic the Synaptic Forgetting Process. Journal of Electronic Materials, 2018, 47, 994-997.	1.0	7
15	Estimation of Beat-to-Beat Interval from Wearable Photoplethysmography Sensor on Different Measurement Sites During Daily Activities. , 2018, , .		1
16	Highly Sensitive ALD SnO ₂ Sensors and the Role of its Thickness in Gas Sensing Capabilities. , 2018, , .		2
17	Building Blocks of a New ALD E-Nose - A First Step: N-Type and P-Type ALD Sensors. , 2018, , .		3
18	Effect of High Temperature Forming Gas Annealing on Electrical Properties of 4H-SiC Lateral MOSFETs with Lanthanum Silicate and ALD SiO ₂ Gate Dielectric. Materials Science Forum, 2018, 924, 482-485.	0.3	1

#	ARTICLE	IF	CITATIONS
19	Room temperature ozone and humidity response evolution of atomic layer deposited SnO ₂ sensors. , 2017, , .		3
20	Optimization of ALD high-k gate dielectric to improve AlGaIn/GaN MOS-HFET DC characteristics and reliability. , 2017, , .		5
21	Electrical Characteristics of SiO ₂ Deposited by Atomic Layer Deposition on 4H-SiC After Nitrous Oxide Anneal. IEEE Transactions on Electron Devices, 2016, 63, 2826-2830.	1.6	20
22	Metal oxide gas sensing characterization by low frequency noise spectroscopy. , 2016, , .		0
23	Room temperature sensing of VOCs by atomic layer deposition of metal oxide. , 2016, , .		3
24	Memristive behavior in BaTiO ₃ /La _{0.7} Sr _{0.3} MnO ₃ heterostructures integrated with semiconductors. MRS Advances, 2016, 1, 275-280.	0.5	1
25	Low-Power Wearable Systems for Continuous Monitoring of Environment and Health for Chronic Respiratory Disease. IEEE Journal of Biomedical and Health Informatics, 2016, 20, 1251-1264.	3.9	159
26	Physical understanding of trends in current collapse with atomic layer deposited dielectrics in AlGaIn/GaN MOS heterojunction FETs. Semiconductor Science and Technology, 2016, 31, 035016.	1.0	7
27	Ultra-low power sensing platform for personal health and personal environmental monitoring. , 2015, , .		6
28	Comparison of Methods for Accurate Characterization of Interface Traps in GaN MOS-HFET Devices. IEEE Transactions on Electron Devices, 2015, 62, 546-553.	1.6	43
29	Flexible Technologies for Self-Powered Wearable Health and Environmental Sensing. Proceedings of the IEEE, 2015, 103, 665-681.	16.4	166
30	Atomic Layer Deposition of SnO ₂ for Selective Room Temperature Low ppb Level O ₃ Sensing. ECS Journal of Solid State Science and Technology, 2015, 4, S3059-S3061.	0.9	22
31	ALD gate dielectrics for improved threshold voltage stability in AlGaIn/GaN MOS-HFETs for power applications. Semiconductor Science and Technology, 2015, 30, 125017.	1.0	11
32	A new AlGaIn/GaN power HFET employing partial deep trench drain structure for high voltage application. , 2015, , .		1
33	Ferroelectric and magnetic properties of multiferroic BiFeO ₃ -La _{0.7} Sr _{0.3} MnO ₃ heterostructures integrated with Si (100). Journal of Applied Physics, 2015, 117, 17D908.	1.1	9
34	Understanding the gradual reset in Pt/Al ₂ O ₃ /Ni RRAM for synaptic applications. Semiconductor Science and Technology, 2015, 30, 105014.	1.0	66
35	Application of AlGaIn/GaN Heterostructures for Ultra-Low Power Nitrogen Dioxide Sensing. ECS Journal of Solid State Science and Technology, 2015, 4, S3034-S3037.	0.9	6
36	Investigation of Lanthanum Silicate Conditions on 4H-SiC MOSFET Characteristics. IEEE Transactions on Electron Devices, 2015, 62, 3781-3785.	1.6	12

#	ARTICLE	IF	CITATIONS
37	High Mobility 4H-SiC Lateral MOSFETs Using Lanthanum Silicate and Atomic Layer Deposited SiO ₂ . IEEE Electron Device Letters, 2015, 36, 312-314.	2.2	23
38	Accurate characterization and understanding of interface trap density trends between atomic layer deposited dielectrics and AlGaIn/GaN with bonding constraint theory. Applied Physics Letters, 2015, 106, 243503.	1.5	14
39	Understanding the influence of E _a and band-offset toward the conductance modulation in Al ₂ O ₃ and HfO ₂ , synaptic RRAM. , 2015, , .		0
40	Design and fabrication of high current AlGaIn/GaN HFET for Gen III solid state transformer. , 2014, , .		4
41	Effect of post deposition annealing for high mobility 4H-SiC MOSFET utilizing lanthanum silicate and atomic layer deposited SiO ₂ . , 2014, , .		1
42	Flash MOSFET operational stability for power converter circuits. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 875-878.	0.8	1
43	High Mobility 4H-SiC MOSFETs Using Lanthanum Silicate Interface Engineering and ALD Deposited SiO ₂ . Materials Science Forum, 2014, 778-780, 557-561.	0.3	13
44	Device Modeling for Understanding AlGaIn/GaN HEMT Gate-Lag. IEEE Transactions on Electron Devices, 2014, 61, 2012-2018.	1.6	33
45	High voltage AlGaIn/GaN HFET employing low taper angle field-plate for stable forward blocking capability. , 2014, , .		1
46	A novel methodology using pulsed-IV for interface or border traps characterization on AlGaIn/GaN MOSFETs. , 2014, , .		4
47	Dual Floating Gate Unified Memory MOSFET With Simultaneous Dynamic and Non-Volatile Operation. IEEE Electron Device Letters, 2014, 35, 48-50.	2.2	4
48	Investigation of intermediate dielectric for dual floating gate MOSFET. , 2013, , .		1
49	Molecular sentinel-on-chip for SERS-based biosensing. Physical Chemistry Chemical Physics, 2013, 15, 6008.	1.3	43
50	Properties of atomic layer deposited dielectrics for AlGaIn/GaN device passivation. Semiconductor Science and Technology, 2013, 28, 074004.	1.0	28
51	Atomic Layer Deposited TiO ₂ thin films for environmental gas sensing. , 2013, , .		0
52	Investigation of Nitrided Atomic-Layer-Deposited Oxides in 4H-SiC Capacitors and MOSFETs. Materials Science Forum, 2013, 740-742, 707-710.	0.3	3
53	Simulation and Experimental Characterization of a Unified Memory Device with Two Floating-Gates. IFIP Advances in Information and Communication Technology, 2013, , 217-233.	0.5	0
54	The Role of Rare Earth Metals on Effective Work Function Modulation of Nickel Fully-Silicided Gate/High- κ Dielectric Stacks for n-Channel Metal Oxide Semiconductor Device Applications. Japanese Journal of Applied Physics, 2012, 51, 011802.	0.8	0

#	ARTICLE	IF	CITATIONS
55	Work function extraction of metal gates with alternate channel materials. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2012, 30, 022202.	0.6	2
56	A novel double floating-gate unified memory device. , 2012, , .		0
57	Atomic Layer Deposition of SiO_2 for AlGaIn/GaN MOS-HFETs. IEEE Electron Device Letters, 2012, 33, 1240-1242.	2.2	37
58	A novel double floating-gate unified memory device. , 2012, , .		2
59	Effects of a High-k Dielectric on the Performance of InGaAs Ballistic Deflection Transistors. IEEE Electron Device Letters, 2012, 33, 1120-1122.	2.2	9
60	Threshold voltage stability comparison in AlGaIn/GaN FLASH MOS-HFETs utilizing charge trap or floating gate charge storage. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 864-867.	0.8	14
61	Normally-off AlGaIn/GaN MOSHFET using ALD SiO_2 tunnel dielectric and ALD HfO_2 charge storage layer for power device application. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 868-870.	0.8	11
62	The Role of Rare Earth Metals on Effective Work Function Modulation of Nickel Fully-Silicided Gate/High-k Dielectric Stacks for n-Channel Metal Oxide Semiconductor Device Applications. Japanese Journal of Applied Physics, 2012, 51, 011802.	0.8	0
63	Multivalued Logic Using a Novel Multichannel GaN MOS Structure. IEEE Electron Device Letters, 2011, 32, 1379-1381.	2.2	6
64	Investigation of the Origin of $V_{T}/V_{m\text{FB}}$ Modulation by La_2O_3 Capping Layer Approaches for NMOS Application: Role of La Diffusion, Effect of Host High-k Layer, and Interface Properties. IEEE Transactions on Electron Devices, 2011, 58, 3106-3115.	1.6	19
65	Impact of AlTaO Dielectric Capping on Device Performance and Reliability for Advanced Metal Gate/High-k PMOS Application. IEEE Transactions on Electron Devices, 2011, 58, 2928-2935.	1.6	1
66	Hybrid Top-Down and Bottom-Up Fabrication Approach for Wafer-Scale Plasmonic Nanoplatfoms. Small, 2011, 7, 727-731.	5.2	25
67	Measurements of generation-recombination effect by low-frequency phase-noise technique in AlGaIn/GaN MOSHFETs. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 1539-1543.	0.8	6
68	Performance improvement of AlGaIn/GaN high electron mobility transistors with atomic layer deposition (ALD) of SiO_2 and HfAlO dielectrics. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 2445-2447.	0.8	8
69	Suppression of dielectric crystallization on metal by introduction of SiO_2 layer for metal floating gate memory blocking oxide. Applied Physics Letters, 2011, 99, 222903.	1.5	1
70	Performance enhancement of AlGaIn/GaN metal-oxide-semiconductor heterojunction field-effect transistor (MOSHFET) with atomic layer deposition (ALD) of high-k HfAlO gate dielectric layer. , 2011, , .		1
71	Investigation of Thermal Stability of High-kappa Interpoly Dielectrics in TaN Metal Floating Gate Memory Structures. , 2011, , .		0
72	Impact of ALD Gate Dielectrics (SiO_2 , HfO_2 , and SiO_2/HAH) on Device Electrical Characteristics and Reliability of AlGaIn/GaN MOSHFET Devices. ECS Transactions, 2011, 41, 445-450.	0.3	11

#	ARTICLE	IF	CITATIONS
73	Introduction to the Special Section on Electronic and Ionic Interfaces to Biomolecules and Cells. IEEE Nanotechnology Magazine, 2010, 9, 268-268.	1.1	0
74	Encapsulation of organic solar cells with ultrathin barrier layers deposited by ozone-based atomic layer deposition. Organic Electronics, 2010, 11, 1896-1900.	1.4	65
75	Normally-off AlGaIn/GaN-on-Si MOSFETs with TaN floating gates and ALD SiO ₂ tunnel dielectrics. , 2010, , .		8
76	Interfacial self cleaning during atomic layer deposition and annealing of HfO ₂ films on native (100)-GaAs substrates. Applied Physics Letters, 2010, 96, .	1.5	52
77	Technique to improve performance of Al ₂ O ₃ interpoly dielectric using a La ₂ O ₃ interface scavenging layer for floating gate memory structures. Applied Physics Letters, 2010, 96, 092905.	1.5	14
78	Platinum Nanoparticles Grown by Atomic Layer Deposition for Charge Storage Memory Applications. Journal of the Electrochemical Society, 2010, 157, H589.	1.3	35
79	Plasmonic Nanoparticles and Nanowires: Design, Fabrication and Application in Sensing. Journal of Physical Chemistry C, 2010, 114, 7480-7488.	1.5	105
80	Energy-band alignment of Al ₂ O ₃ and HfAlO gate dielectrics deposited by atomic layer deposition on 4H-SiC. Applied Physics Letters, 2010, 96, .	1.5	66
81	Methodologies for Developing Surface-Enhanced Raman Scattering (SERS) Substrates for Detection of Chemical and Biological Molecules. IEEE Sensors Journal, 2010, 10, 608-616.	2.4	30
82	Low-Frequency Noise Measurements of AlGaIn/GaN Metal-Oxide-Semiconductor Heterostructure Field-Effect Transistors With HfAlO Gate Dielectric. IEEE Electron Device Letters, 2010, 31, 1041-1043.	2.2	21
83	Ultimate scalability of TaN metal floating gate with incorporation of high-K blocking dielectrics for Flash memory applications. , 2010, , .		14
84	Sub-2 nm Size-Tunable High-Density Pt Nanoparticle Embedded Nonvolatile Memory. IEEE Electron Device Letters, 2009, 30, 1362-1364.	2.2	27
85	Schottky Barrier Height of Erbium Silicide on $\text{Si}_{1-x}\text{C}_x$. IEEE Electron Device Letters, 2009, 30, 949-951.	2.2	6
86	High-mobility enhancement-mode 4H-SiC lateral field-effect transistors utilizing atomic layer deposited Al ₂ O ₃ gate dielectric. Applied Physics Letters, 2009, 95, .	1.5	39
87	Gate Stack Reliability of High-Mobility 4H SiC Lateral MOSFETs with Deposited Al ₂ O ₃ Gate Dielectric. Materials Research Society Symposia Proceedings, 2009, 1195, 155.	0.1	0
88	Atomic Layer Deposition of Hafnium Dioxide on TiN and Self-Assembled Monolayer Molecular Film. Journal of the Electrochemical Society, 2009, 156, H561.	1.3	3
89	Interface and Electrical Properties of Atomic-layer-deposited HfAlO Gate Dielectric for N-channel GaAs MOSFETs. Materials Research Society Symposia Proceedings, 2009, 1155, 1.	0.1	0
90	Erbium Silicide Formation on Si _{1-x} C _x Epitaxial Layers. Journal of the Electrochemical Society, 2009, 156, H378.	1.3	5

#	ARTICLE	IF	CITATIONS
91	Platinum Germanosilicide Contacts Formed on Strained and Relaxed $\text{Si}_{1-x}\text{Ge}_x$ Layers. IEEE Transactions on Electron Devices, 2009, 56, 1220-1227.	1.6	8
92	Tuning of the Platinum Silicide Schottky Barrier Height on n-Type Silicon by Sulfur Segregation. IEEE Electron Device Letters, 2009, 30, 331-333.	2.2	31
93	Transparent indium gallium zinc oxide transistor based floating gate memory with platinum nanoparticles in the gate dielectric. Applied Physics Letters, 2009, 94, .	1.5	91
94	Fabrication of large area nano-rings for MRAM application. Microelectronic Engineering, 2008, 85, 1555-1560.	1.1	7
95	Large area nanorings fabricated using an atomic layer deposition Al_2O_3 spacer for magnetic random access memory application. Nanotechnology, 2008, 19, 265301.	1.3	14
96	Effect of GaAs Surface Treatments on Lanthanum Silicate High-K Dielectric Gate Stack Properties. Materials Research Society Symposia Proceedings, 2008, 1073, 1.	0.1	2
97	Investigation of VT Shift Mechanism of High-K Dielectrics caused by Lanthanum Capping for NMOS and Tantalum Capping for PMOS Devices. ECS Transactions, 2008, 13, 123-130.	0.3	3
98	Impact of elemental arsenic on electrical characteristics of metal-oxide-semiconductor capacitors on GaAs using atomic-layer deposited HfO_2 gate dielectric. Applied Physics Letters, 2008, 92, .	1.5	24
99	Modulating indium gallium zinc oxide transistor characteristics with discrete redox states of molecules embedded in the gate dielectric. Applied Physics Letters, 2008, 92, 223304.	1.5	7
100	Electrical characteristics of metal-oxide-semiconductor capacitors on p-GaAs using atomic layer deposition of ultrathin HfAlO gate dielectric. Applied Physics Letters, 2008, 93, 193504.	1.5	26
101	Impact of metal gates on remote phonon scattering in titanium nitride/hafnium dioxide n-channel metal-oxide-semiconductor field effect transistors—low temperature electron mobility study. Journal of Applied Physics, 2007, 102, .	1.1	41
102	Valence band tunneling model for charge transfer of redox-active molecules attached to n- and p-silicon substrates. Applied Physics Letters, 2007, 90, 142113.	1.5	16
103	The effects of nickel germanosilicide contacts on the biaxial compressive stress in thin epitaxial silicon-germanium alloys on silicon. Applied Physics Letters, 2007, 91, 142118.	1.5	8
104	A molecular memory device formed by HfO_2 encapsulation of redox-active molecules. Applied Physics Letters, 2007, 91, 173111.	1.5	11
105	Characteristics of Ni/Gd FUSI for NMOS Gate Electrode Applications. IEEE Electron Device Letters, 2007, 28, 555-557.	2.2	8
106	Analysis of boron strain compensation in silicon-germanium alloys by Raman spectroscopy. Applied Physics Letters, 2006, 88, 202114.	1.5	30
107	Hybrid silicon/molecular FETs: a study of the interaction of redox-active molecules with silicon MOSFETs. IEEE Nanotechnology Magazine, 2006, 5, 258-264.	1.1	13
108	Influence of oxygen diffusion through capping layers of low work function metal gate electrodes. IEEE Electron Device Letters, 2006, 27, 228-230.	2.2	9

#	ARTICLE	IF	CITATIONS
109	Large-area long-range ordered anisotropic magnetic nanostructure fabrication by photolithography. Nanotechnology, 2006, 17, 4909-4911.	1.3	23
110	A Systematic Approach of Understanding and Retaining Pmos Compatible Work Function of Metal Electrodes On HfO ₂ Gate Dielectrics. Materials Research Society Symposia Proceedings, 2006, 917, 1.	0.1	1
111	High-Temperature Stability of Lanthanum Silicate Gate Dielectric MIS Devices with Ta and TaN Electrodes. Journal of the Electrochemical Society, 2006, 153, F210.	1.3	5
112	Impact of Heavy Boron Doping and Nickel Germanosilicide Contacts on Biaxial Compressive Strain in Pseudomorphic Silicon-Germanium Alloys on Silicon. Materials Research Society Symposia Proceedings, 2006, 913, 1.	0.1	0
113	On the Issue of Work Function Tuning of Nickel Silicide Gates. ECS Transactions, 2006, 3, 317-331.	0.3	3
114	Workfunction Tuning of Nickel Silicide by Varying Nickel and Silicon Composition. ECS Transactions, 2006, 1, 295-303.	0.3	0
115	Electrical and Physical Analysis of MoTa Alloy for Gate Electrode Applications. Journal of the Electrochemical Society, 2006, 153, G417.	1.3	14
116	Work Function Tuning Via Interface Dipole by Ultrathin Reaction Layers Using AlTa and AlTa _N Alloys. IEEE Electron Device Letters, 2006, 27, 731-733.	2.2	24
117	Critical thickness of heavily boron-doped silicon-germanium alloys. Applied Physics Letters, 2006, 89, 202118.	1.5	4
118	Feasibility of Dipole Based Work Function Tuning for Sub-1nm EOT Metal Gated High-K Stacks. ECS Transactions, 2006, 3, 275-287.	0.3	0
119	Towards the Fabrication of Ultra-Thin SOI on Si (001) using Epitaxial Oxide and Epitaxial Semiconductor Growth Processes. ECS Transactions, 2006, 3, 449-460.	0.3	3
120	Properties of Ta _{0.5} Mo alloy gate electrode for n-MOSFET. Journal of Materials Science, 2005, 40, 2693-2695.	1.7	14
121	Redox-active monolayers on nano-scale silicon electrodes. Nanotechnology, 2005, 16, 257-261.	1.3	16
122	Approach for investigating lateral conduction in self-assembled monolayers. Applied Physics Letters, 2005, 87, 262115.	1.5	1
123	Physical and electrical analysis of Ru _x Y _y alloys for gate electrode applications. Applied Physics Letters, 2005, 86, 053502.	1.5	14
124	Electrical Characteristics of HfO ₂ Dielectrics with Ru Metal Gate Electrodes. Journal of the Electrochemical Society, 2005, 152, F138.	1.3	29
125	Investigation of work function tuning using multiple layer metal gate electrodes stacks for complementary metal-oxide-semiconductor applications. Applied Physics Letters, 2005, 87, 223503.	1.5	10
126	Impact of Ge on integration of HfO ₂ and metal gate electrodes on strained Si channels. Applied Physics Letters, 2005, 87, 071903.	1.5	7

#	ARTICLE	IF	CITATIONS
127	Evaluation of nickel and molybdenum silicides for dual gate complementary metal-oxide semiconductor application. Applied Physics Letters, 2005, 86, 022105.	1.5	9
128	Properties of Functionalized Redox-Active Monolayers on Thin Silicon Dioxide—A Study of the Dependence of Retention Time on Oxide Thickness. IEEE Nanotechnology Magazine, 2005, 4, 278-283.	1.1	12
129	Synthesis and Film-Forming Properties of Ethynylporphyrins. Chemistry of Materials, 2005, 17, 3728-3742.	3.2	46
130	Work function tuning of nickel silicide by co-sputtering nickel and silicon. Applied Physics Letters, 2005, 87, 171908.	1.5	27
131	Characteristics of TaSi _x N _y thin films as gate electrodes for dual gate Si-complementary metal-oxide-semiconductor devices. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2004, 22, 175.	1.6	15
132	Multiple-bit storage properties of porphyrin monolayers on SiO ₂ . Applied Physics Letters, 2004, 85, 1829-1831.	1.5	46
133	A Capacitance-Based Methodology for Work Function Extraction of Metals on High- κ . IEEE Electron Device Letters, 2004, 25, 420-423.	2.2	104
134	Synthesis of Porphyrins Bearing Hydrocarbon Tethers and Facile Covalent Attachment to Si(100). Journal of Organic Chemistry, 2004, 69, 5568-5577.	1.7	58
135	Reliability of High-K Dielectrics and Its Dependence on Gate Electrode and Interfacial / High-K Bi-Layer Structure. Microelectronics Reliability, 2004, 44, 1513-1518.	0.9	5
136	Stability of Ru- and Ta-based metal gate electrodes in contact with dielectrics for Si-CMOS. Physica Status Solidi (B): Basic Research, 2004, 241, 2253-2267.	0.7	16
137	Multibit Memory Using Self-Assembly of Mixed Ferrocene/Porphyrin Monolayers on Silicon. Advanced Materials, 2004, 16, 133-137.	11.1	111
138	Porphyrins Bearing Arylphosphonic Acid Tethers for Attachment to Oxide Surfaces.. ChemInform, 2004, 35, no.	0.1	0
139	Porphyrins Bearing Mono or Tripodal Benzylphosphonic Acid Tethers for Attachment to Oxide Surfaces.. ChemInform, 2004, 35, no.	0.1	0
140	Porphyrin Architectures Tailored for Studies of Molecular Information Storage. Journal of Organic Chemistry, 2004, 69, 6739-6750.	1.7	64
141	Porphyrins Bearing Mono or Tripodal Benzylphosphonic Acid Tethers for Attachment to Oxide Surfaces. Journal of Organic Chemistry, 2004, 69, 1453-1460.	1.7	79
142	Porphyrins Bearing Arylphosphonic Acid Tethers for Attachment to Oxide Surfaces. Journal of Organic Chemistry, 2004, 69, 1444-1452.	1.7	71
143	A simulation study to evaluate the feasibility of midgap workfunction metal gates in 25 nm bulk CMOS. IEEE Electron Device Letters, 2003, 24, 707-709.	2.2	11
144	Effect of the composition on the electrical properties of TaSi _x N _y metal gate electrodes. IEEE Electron Device Letters, 2003, 24, 439-441.	2.2	24

#	ARTICLE	IF	CITATIONS
145	Thermal Stability of TaSi _x N _y Films Deposited by Reactive Sputtering on SiO ₂ . Journal of the Electrochemical Society, 2003, 150, F79.	1.3	14
146	Electrical characterization of redox-active molecular monolayers on SiO ₂ for memory applications. Applied Physics Letters, 2003, 83, 198-200.	1.5	59
147	Electrical characteristics of TaSi _x N _y /SiO ₂ /Si structures by Fowlerâ€”Nordheim current analysis. Applied Physics Letters, 2002, 80, 1403-1405.	1.5	27
148	Electrical properties of Ru-based alloy gate electrodes for dual metal gate Si-CMOS. IEEE Electron Device Letters, 2002, 23, 354-356.	2.2	70
149	Issues in High- κ Gate Stack Interfaces. MRS Bulletin, 2002, 27, 212-216.	1.7	76
150	Capacitance and conductance characterization of ferrocene-containing self-assembled monolayers on silicon surfaces for memory applications. Applied Physics Letters, 2002, 81, 1494-1496.	1.5	98
151	The Effects of Nitrogen on Electrical and Structural Properties in TaSi _x N _y /SiO ₂ /p-Si MOS Capacitors. Materials Research Society Symposia Proceedings, 2002, 716, 861.	0.1	2
152	Promising Gate Stacks with Ru & RuO ₂ Gate Electrodes and Y-silicate Dielectrics. Materials Research Society Symposia Proceedings, 2001, 670, 1.	0.1	3
153	Electrical properties of Ru and RuO ₂ gate electrodes for Si-PMOSFET with ZrO ₂ and Zr-silicate dielectrics. Journal of Electronic Materials, 2001, 30, 1493-1498.	1.0	16
154	N and P metal oxide semiconductor field effect transistor characteristics of hafnium-doped SiO ₂ gate dielectrics. Journal of Electronic Materials, 2001, 30, 1499-1505.	1.0	4
155	Study of low-frequency charge pumping on thin stacked dielectrics. IEEE Transactions on Electron Devices, 2001, 48, 2754-2762.	1.6	26
156	Use of metalâ€”oxideâ€”semiconductor capacitors to detect interactions of Hf and Zr gate electrodes with SiO ₂ and ZrO ₂ . Applied Physics Letters, 2001, 78, 4166-4168.	1.5	79
157	Characteristics of metalorganic remote plasma chemical vapor deposited Al ₂ O ₃ gate stacks on SiC metalâ€”oxideâ€”semiconductor devices. Applied Physics Letters, 2001, 79, 973-975.	1.5	30
158	Characterization of RuO ₂ electrodes on Zr silicate and ZrO ₂ dielectrics. Applied Physics Letters, 2001, 78, 1134-1136.	1.5	62
159	Electrical properties of RuO ₂ gate electrodes for dual metal gate Si-CMOS. IEEE Electron Device Letters, 2000, 21, 593-595.	2.2	53
160	A Lowâ€”Thermalâ€”Budget In Situ Doped Multilayer Silicon Epitaxy Process for MOSFET Channel Engineering. Journal of the Electrochemical Society, 1999, 146, 1189-1196.	1.3	4
161	Bonding constraints and defect formation at interfaces between crystalline silicon and advanced single layer and composite gate dielectrics. Applied Physics Letters, 1999, 74, 2005-2007.	1.5	156
162	Electrical and reliability properties of thin silicon oxinitride dielectrics formed by low pressure rapid thermal chemical vapor deposition. Solid-State Electronics, 1997, 41, 1051-1055.	0.8	1

#	ARTICLE	IF	CITATIONS
163	High quality gate dielectrics formed by rapid thermal chemical vapor deposition of silane and nitrous oxide. <i>Journal of Electronic Materials</i> , 1996, 25, 527-535.	1.0	8
164	Integration of Plasma-Assisted and Rapid Thermal Processing for Low-Thermal Budget Preparation of Ultra-Thin Dielectrics for Stacked-Gate Device Structures. <i>Japanese Journal of Applied Physics</i> , 1994, 33, 7061-7070.	0.8	8
165	Selective Removal of Silicon-Germanium: Chemical and Reactive Ion Etching. <i>Materials Research Society Symposia Proceedings</i> , 1993, 298, 157.	0.1	1
166	Characterization of Oxygen-Doped and Non-Oxygen-Doped Polysilicon Films Prepared by Rapid Thermal Chemical Vapor Deposition. <i>Materials Research Society Symposia Proceedings</i> , 1993, 303, 49.	0.1	2
167	Robust ternary metal gate electrodes for dual gate CMOS devices. , 0, , .		16
168	Improved Threshold Voltage Instability in 4H-SiC MOSFETs with Atomic Layer Deposited SiO ₂ . <i>Materials Science Forum</i> , 0, 924, 498-501.	0.3	1